

Abstract

The present invention provides a testing system for plasma properties in a reaction chamber, a processing apparatus for a semiconductor device, a testing method for plasma properties in a reaction chamber, and a computer-readable storage medium. The testing system comprises: at least two sampling paths, used to respectively collect voltage signals of a top cover of the reaction chamber; a voltage processing module, connected to a second sampling path, for shifting a phase of the voltage signal thereof by 180° , to obtain a second voltage signal, and adding the second voltage signal to a first voltage signal of an original phase on a first sampling path, to obtain a third voltage signal filtered out of alternating-current noise; and a testing module, connected to the voltage processing module, to acquire the third voltage signal, and determine the plasma properties in the reaction chamber according to the third voltage signal. The present invention can filter out alternating-current noise in a voltage of a top cover of a reaction chamber, thereby improving the accuracy of plasma properties testing results.

(FIG. 1)